

TIP29 SERIES (TIP29/29A/29B/29C)

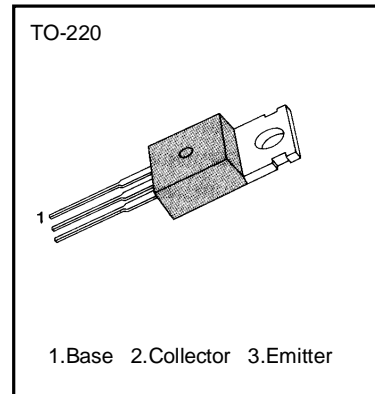
NPN EPITAXIAL SILICON TRANSISTOR

MEDIUM POWER LINEAR SWITCHING APPLICATIONS

• Complementary to TIP30/30A/30B/30C

ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	Rating	Unit	
Collector Emitter Voltage	V_{CBO}	TIP29	40	V
		TIP29A	60	V
		TIP29B	80	V
		TIP29C	100	V
Collector Emitter Voltage	V_{CEO}	TIP29	40	V
		TIP29A	60	V
		TIP29B	80	V
		TIP29C	100	V
Emitter-Base Voltage	V_{EBO}	5	V	
Collector Current (DC)	I_C	1	A	
Collector Current (Pulse)	I_C	3	A	
Base Current	I_B	0.4	A	
Collector Dissipation ($T_C=25^\circ\text{C}$)	P_C	30	W	
Collector Dissipation ($T_A=25^\circ\text{C}$)	P_C	2	W	
Junction Temperature	T_J	150	$^\circ\text{C}$	
Storage Temperature	T_{STG}	-65 ~ 150	$^\circ\text{C}$	



ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$)

Characteristic	Symbol	Test Conditions	Min	Max	Unit
*Collector Emitter Sustaining Voltage	$BV_{CEO(sus)}$	$I_C = 30\text{mA}, I_B = 0$	TIP29	40	V
: TIP29A			60	V	
: TIP29B			80	V	
: TIP29C			100	V	
Collector Cutoff Current	I_{CEO}	$V_{CE} = 30\text{V}, I_B = 0$	TIP29/29A	0.3	mA
: TIP29B/29C			0.3	mA	
Collector Cutoff Current	I_{CES}	$V_{CE} = 40\text{V}, V_{EB} = 0$	TIP29	200	μA
			: TIP29A	200	μA
			: TIP29B	200	μA
			: TIP29C	200	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$		1.0	mA
*DC Current Gain	h_{FE}	$V_{CE} = 4\text{V}, I_C = 0.2\text{A}$	40		
		$V_{CE} = 4\text{V}, I_C = 1\text{A}$	15	75	
*Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 1\text{A}, I_B = 125\text{mA}$		0.7	V
*Base Emitter Saturation Voltage	$V_{BE(on)}$	$V_{CE} = 4\text{V}, I_C = 1\text{A}$		1.3	V
Current Gain Bandwidth Product	f_T	$V_{CE} = 10\text{V}, I_C = 200\text{mA}$ $f = 1\text{MHz}$	3.0		MHz

* Pulse Test : $PW \leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

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